

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE20ND07U uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED! 100% ΔVds TESTED!

General Features

● V_{DS} = 20V,I_D =7A

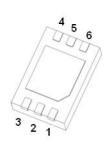
 $R_{DS(ON)}$ < 16m Ω @ V_{GS} =4.5V

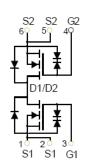
 $R_{DS(ON)}$ < 20m Ω @ V_{GS} =2.5V

 $R_{DS(ON)}$ < 35m Ω @ V_{GS} =1.8V

- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- ESD Rating: 2000V HBM

DFN 2X3-6L





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
20ND07	NCE20ND07U	DFN2X3-6L	Ø180mm		3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	7	Α
Drain Current-Pulsed (Note 1)	I _{DM}	30	Α
Maximum Power Dissipation	P _D	1.5	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	°C/W

NCE20ND07U

Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics				•		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)				•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.5	0.7	0.9	V
		V _{GS} =4.5V, I _D =7A	-	11.5	16	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =6.5A	-	14.5	20	mΩ
		V _{GS} =1.8V, I _D =6A	-	19.5	35	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =7A	-	20	-	S
Dynamic Characteristics (Note4)				•		
Input Capacitance	C _{lss}	1/ 40)/// 0)/	-	811.1	-	PF
Output Capacitance	Coss	V_{DS} =10V, V_{GS} =0V, F=1.0MHz	-	183.6	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	131.2	-	PF
Switching Characteristics (Note 4)			•	•		
Turn-on Delay Time	t _{d(on)}		-	6		nS
Turn-on Rise Time	t _r	V_{DD} =10V, R_L =1.4 Ω	-	13		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =5 V , R_{GEN} =3 Ω	-	52		nS
Turn-Off Fall Time	t _f		-	16		nS
Total Gate Charge	Qg	101/1 74	-	14.2		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=10V,I_{D}=7A,$	-	1.4	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	4.5	-	nC
Drain-Source Diode Characteristics			l			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =7A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	7	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

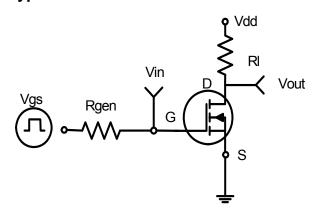
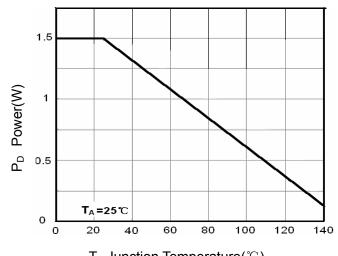


Figure 1:Switching Test Circuit



 T_J -Junction Temperature(°C) Figure 3 Power Dissipation

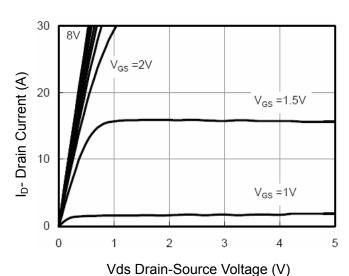


Figure 5 Output Characteristics

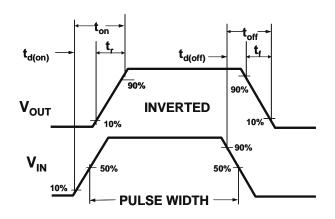


Figure 2:Switching Waveforms

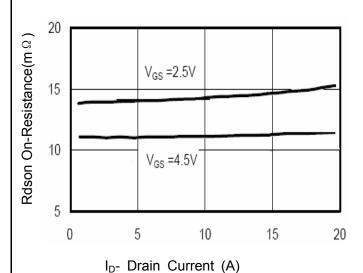


Figure 6 Drain-Source On-Resistance

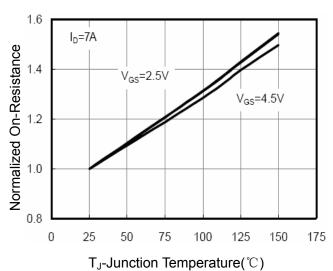
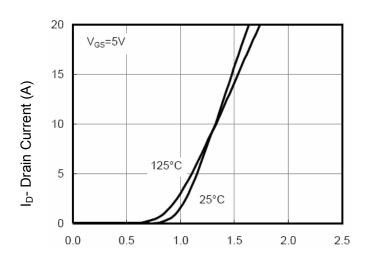


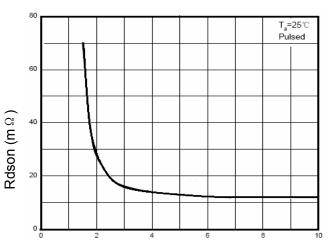
Figure 8 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

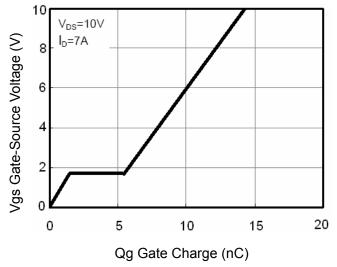
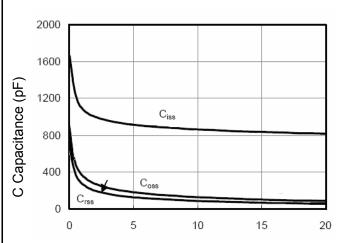
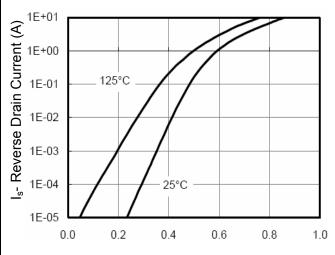


Figure 11 Gate Charge



Vds Drain-Source Voltage (V)

Figure 8 Capacitance vs Vds



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

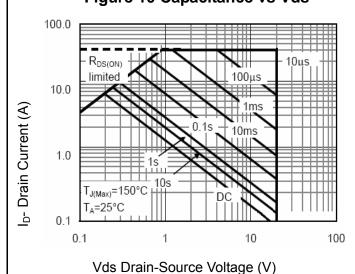


Figure 13 Safe Operation Area





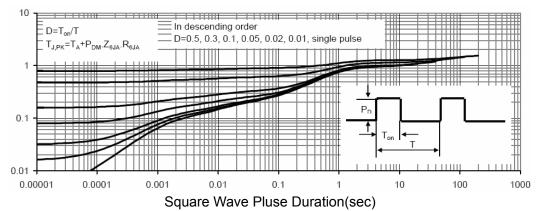
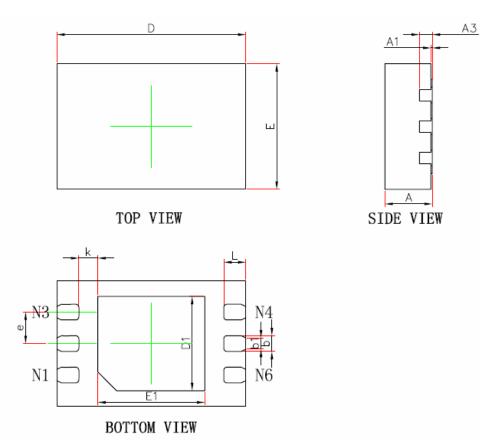


Figure 14 Normalized Maximum Transient Thermal Impedance



DFN2X3-6L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	MIN.	MAX.	MIN.	MAX.	
Α	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A3	0.203REF.		0.008REF.		
D	2.950	3.050	0.116	0.120	
Е	1.950	2.050	0.077	0.081	
D1	1.400	1.600	0.055	0.063	
E1	1.600	1.800	0.063	0.071	
b	0.200	0.300	0.008	0.012	
b1	0.180REF.		0.007REF.		
е	0.500TYP.		0.020TYP.		
k	0.200MIN.		0.008MIN.		
L	0.300	0.400	0.012	0.016	

http://www.ncepower.com

NCE20ND07U

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